

Title (en)

Scalable LED with improved current spreading structures

Title (de)

Skalierbare LED mit verbesserten Stromverteilungsstrukturen

Title (fr)

DEL évolutive dotée de structures de propagation de courant améliorées

Publication

EP 2337095 A3 20140924 (EN)

Application

EP 10183656 A 20001122

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- US 16833899 P 19991201
- US 72135200 A 20001121
- EP 00979221 A 20001122
- US 0032167 W 20001122

Abstract (en)

[origin: EP2337096A2] An LED with improved current spreading structures that provide enhanced current injection into the LED's active layer (14), improving its power and luminous flux. The current spreading structures can be used in LEDs larger than conventional LEDs while maintaining the enhanced current injection. The invention is particularly applicable to LEDs having insulating substrates (12) but can also reduce the series resistance of LEDs having conductive substrates. The improved structures comprise conductive fingers (20a, 20b, 22) that form cooperating conductive paths that ensure that current spreads from the contacts (19, 21), into the fingers (20a, 20b, 22) and uniformly spreads through the oppositely doped layers (15, 16). The current then spreads to the active layer (14) to uniformly inject electrons and holes throughout the active layer (14), which recombine to emit light.

IPC 8 full level

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Citation (search report)

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